

SOD-323 Plastic-Encapsulate Diode

BAS316 SCHOTTKEY BARRIER DIODE

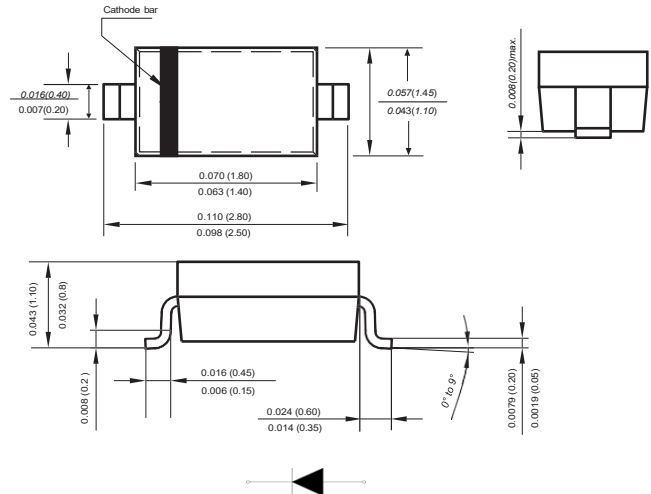
FEATURES

- For surface mounted applications
- Fast reverse recovery time
- Ideal for automated placement

Marking



SOD-323



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

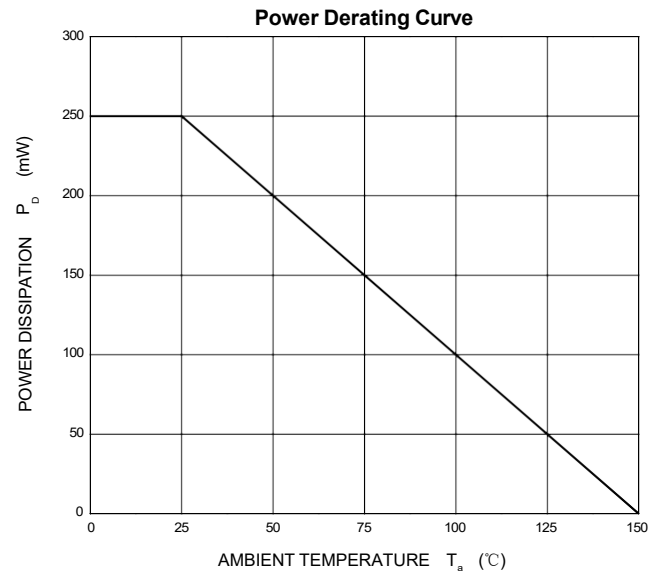
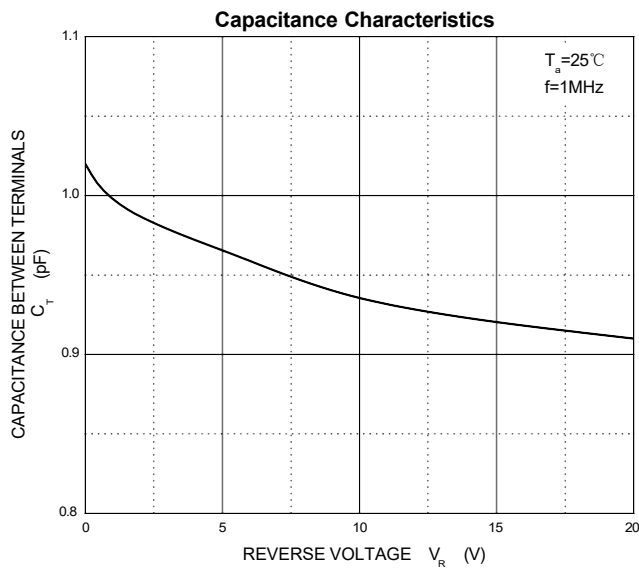
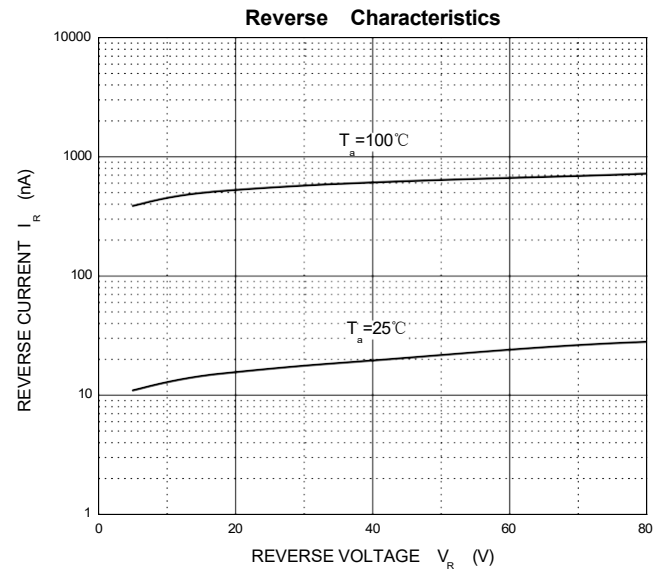
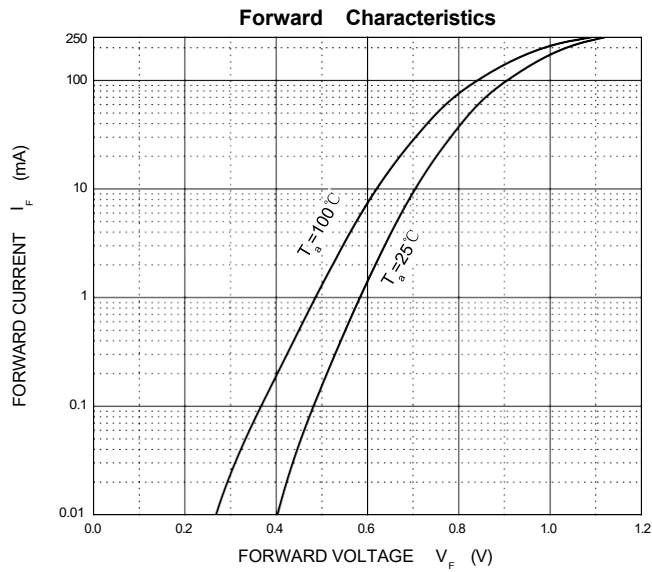
Parameter	Symbo	Limit	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Peak Repetitive Peak Reverse Voltage	V_{RMS}	75	V
Average Rectified Output Current Ta=25°C	I_F	250	mA
Non-reptitive Peak Forward Surge Current at 1s at 1ms at 1us	I_{FSM}	0.5 1 4	A
Repetitive peak forward current	I_{FRM}	500	mA
Power Dissipation	P_{TOT}	400	mW
Operating and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	BAS316	Unit
Reverse voltage leakage current	I_R	$V_R=25V, T_J=25^\circ C$ $V_R=75V, T_J=25^\circ C$ $V_R=25V, T_J=150^\circ C$ $V_R=75V, T_J=150^\circ C$	0.03 1.0 30 50	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$	0.715 0.855 1.00 1.25	V
Typical Junction Capacitance	C_J	$V_R=0, f=1MHz$	2	pF
Reveres recovery time(1)	t_{rr}	$I_F=I_R=10mA, I_{rr}=0.1 \times I_R, R_L=100\Omega$	4	ns

(1) Measured with $I_F=I_R=10mA, I_{rr}=0.1 \times I_R, R_L=100\Omega$

Typical Characteristics



The curve above is for reference only.